

What is claimed is:

1. An active matrix display device comprising:

a thin-film transistor that is driven being supplied with a scanning signal from the gate signal line, the thin-film transistor having a gate electrode that is made of a material different than the gate signal line and has a part of which is directly laid on or under the gate signal line to establish electrical connection; and

2. An active matrix display device comprising:

a thin-film transistor that is driven being supplied with a scanning signal from the gate signal line, the thin-film transistor having a gate electrode that is made of a material different than the gate signal line and has a part of which is electrically connected to the gate signal line; and

3. An active matrix display device comprising:

a thin-film transistor that is driven being supplied with a scanning signal from the gate signal line, the thin-film transistor having a gate electrode that is made of a material different than the gate signal line and that overlaps with the gate signal line; and

a pixel electrode that is supplied with a video signal from the drain signal line via the thin-film transistor.

4. An active matrix display device comprising:

a substrate having a gate signal line and a drain signal line;

a thin-film transistor that is driven being supplied with a scanning signal from the gate signal line, the thin-film transistor having a gate electrode having a portion that is made of a layer different than the gate signal line and that is electrically connected to the gate signal line; and

a pixel electrode that is supplied with a video signal from the drain signal line via the thin-film transistor.

5. An active matrix display device comprising:

a display area including a set of pixel regions each having a first thin-film transistor; and

a driving circuit forming area located outside the display area and having second thin-film transistors, wherein:

a gate electrode of the first thin-film transistor is made of a material different than a gate signal line and is electrically connected to the gate signal line;

a gate electrode of each of the second thin-film transistors is made of a material different than a wiring layer or electrode and electrically connected to the wiring layer or electrode;

the gate electrode of the first thin-film transistor is made of the same material as that of each of the second thin-film transistors; and

the gate signal line is made of the same material as the wiring layer or electrode.

6. The active matrix display device according to any one of claims 1 to 4, wherein the gate signal line is made of aluminum.

7. The active matrix display device according to any one of claims 1 to 4, wherein a semiconductor layer of the first thin-film transistor and/or each of the second thin-film transistors is made of polysilicon.

8. The active matrix display device according to any one of claims 1 to 4, wherein metal layers are formed on a drain region and a source region, respectively, of the first thin-film transistor and/or each of the second thin-film transistors, and portions of the respective metal layers are exposed through respective contact holes that are formed through a passivation film that covers the thin-film transistor.

9. The active matrix display device according to claim 8, wherein the metal layers are formed at the same time as a

gate electrode of the thin-film transistor is formed.

10. The active matrix ~~display~~ device according to any one of claims 1-5, wherein ~~the~~ active matrix device is liquid crystal device.

Sub-7  
A2

add  
A3

09919916 080201  
102080 91651660